查询BT151U-500C供应商

GENERAL DESCRIPTION

Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

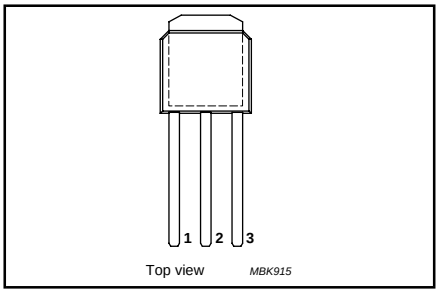
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT151U-	**500C**	**650C**	**800C**	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages	500	650	800	V
$I_{T(AV)}$	Average on-state current	7.5	7.5	7.5	A
$I_{T(RMS)}$	RMS on-state current	12	12	12	A
I_{TSM}	Non-repetitive peak on-state current	100	100	100	A

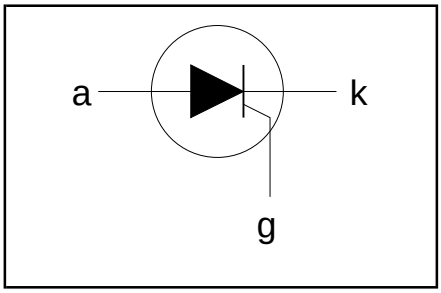
PINNING - SOT533, (I-PAK)

PIN NUMBER	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500C	**-650C**	**-800C**	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages		-	500[1]	650[1]	800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 104$ ˚C	-	7.5			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	12			A
I_{TSM}	Non-repetitive peak on-state current	half sine wave; $T_j = 25$ ˚C prior to surge					
		t = 10 ms	-	100			A
		t = 8.3 ms	-	110			A
I^2t	I^2t for fusing	t = 10 ms	-	50			A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20$ A; $I_G = 50$ mA; $dI_G/dt = 50$ mA/µs	-	50			A/µs
I_{GM}	Peak gate current		-	2			A
V_{RGM}	Peak reverse gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			˚C
T_j	Junction temperature		-	125			˚C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	1.3	K/W
						K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	70	-	K/W

STATIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	V_D = 12 V; I_T = 0.1 A	-	2	15	mA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A	-	10	40	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A	-	7	20	mA
V_T	On-state voltage	I_T = 23 A	-	1.44	1.75	V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.6	1.5	V
		V_D = $V_{DRM(max)}$; I_T = 0.1 A; T_j = 125 ˚C	0.25	0.4	-	V
I_D, I_R	Off-state leakage current	V_D = $V_{DRM(max)}$; V_R = $V_{RRM(max)}$; T_j = 125 ˚C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 ˚C; exponential waveform				
		Gate open circuit	50	130	-	V/µs
		R_{GK} = 100 Ω	200	1000	-	V/µs
t_{gt}	Gate controlled turn-on time	I_{TM} = 40 A; V_D = $V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	µs
t_q	Circuit commutated turn-off time	V_D = 67% $V_{DRM(max)}$; T_j = 125 ˚C; I_{TM} = 20 A; V_R = 25 V; dI_{TM}/dt = 30 A/µs; dV_D/dt = 50 V/µs; R_{GK} = 100 Ω	-	70	-	µs

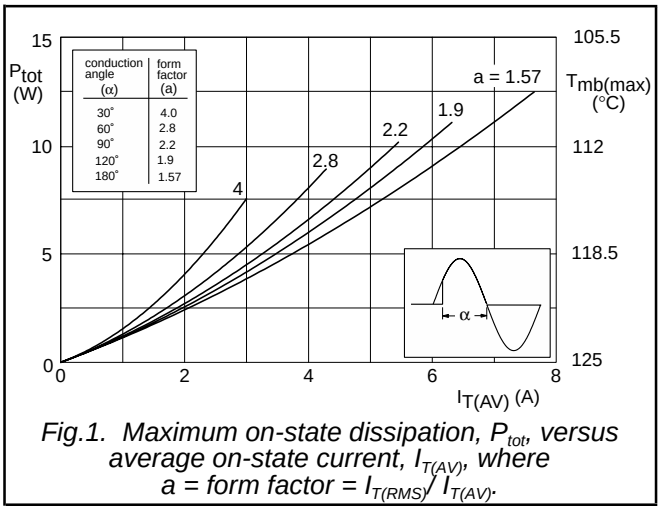


Fig.1. Maximum on-state dissipation, P_{tot}, versus average on-state current, $I_{T(AV)}$, where a = form factor = $I_{T(RMS)}$/ $I_{T(AV)}$.

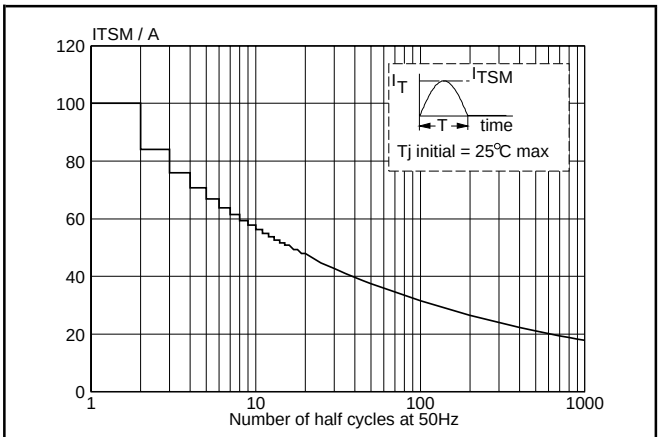


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

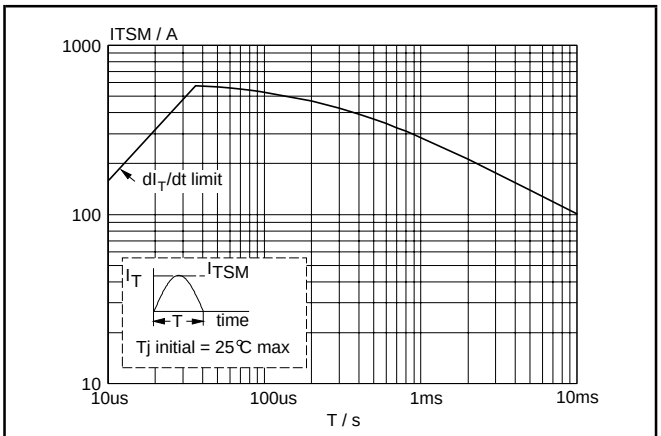


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus pulse width t_p, for sinusoidal currents, $t_p \leq 10$ms.

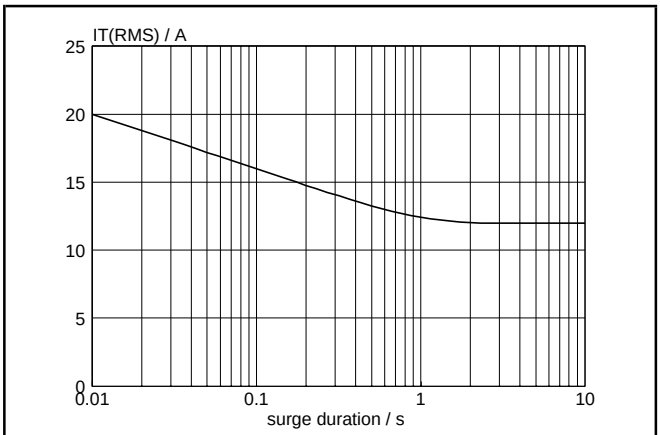


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \leq 100$ ˚C.

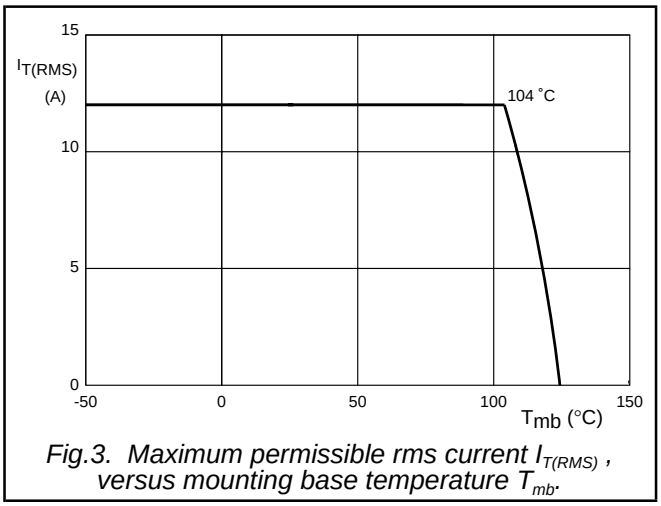


Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb}.

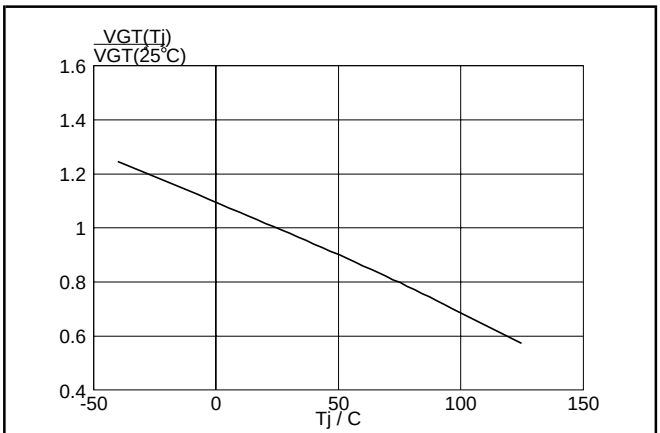


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)$/ V_{GT}(25˚C), versus junction temperature T_j.

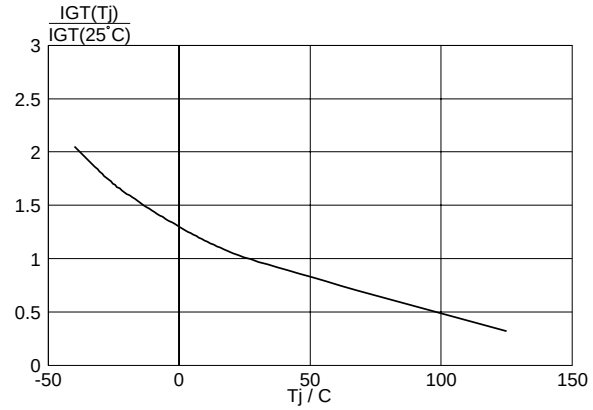


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/ I_{GT}(25^{\circ}C)$, versus junction temperature T_j.

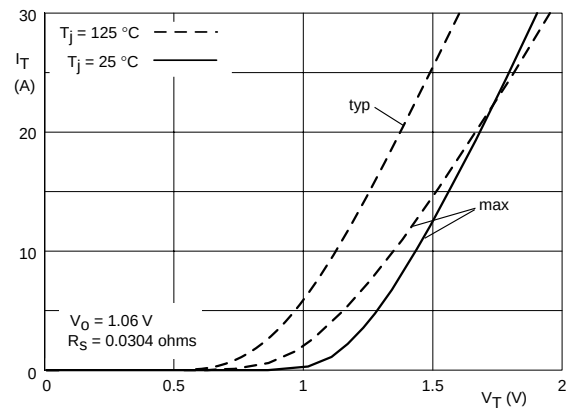


Fig.10. Typical and maximum on-state characteristic.

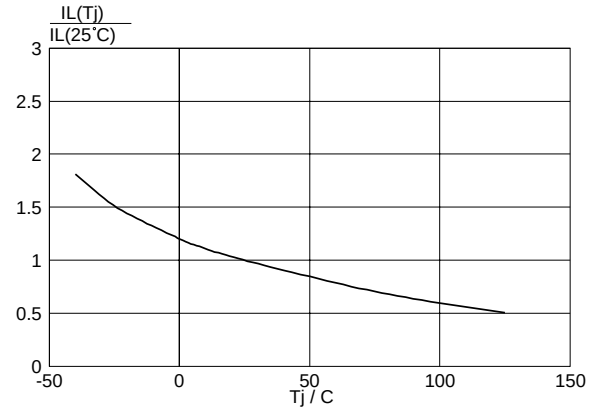


Fig.8. Normalised latching current $I_L(T_j)/ I_L(25^{\circ}C)$, versus junction temperature T_j.

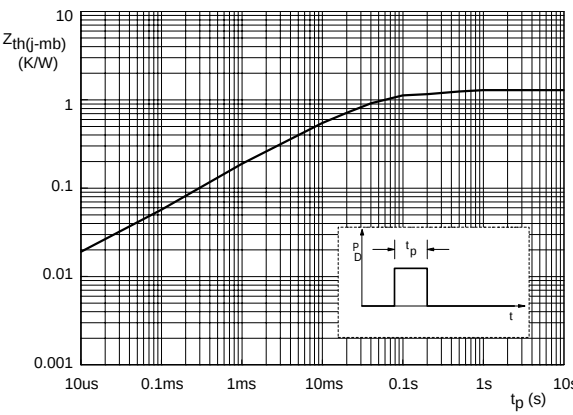


Fig.11. Transient thermal impedance $Z_{th\ j\text{-}mb}$, versus pulse width t_p.

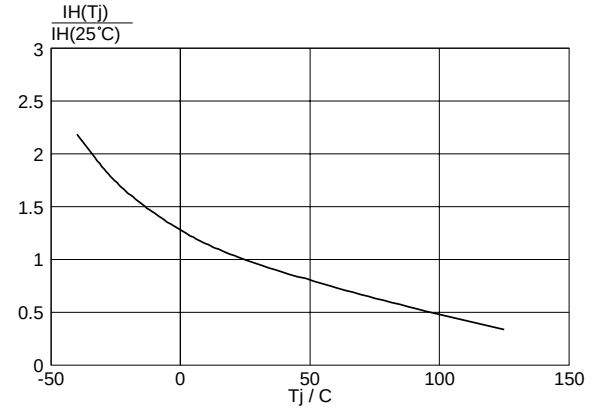


Fig.9. Normalised holding current $I_H(T_j)/ I_H(25^{\circ}C)$, versus junction temperature T_j.

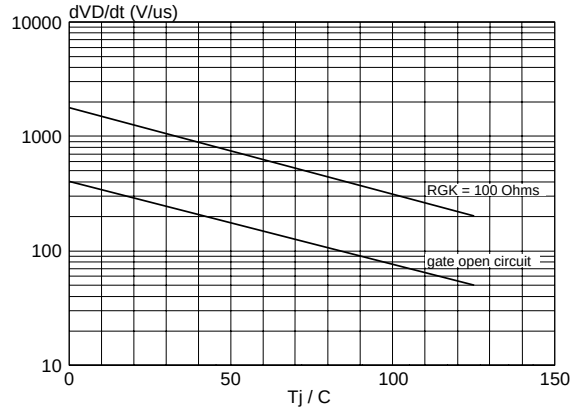
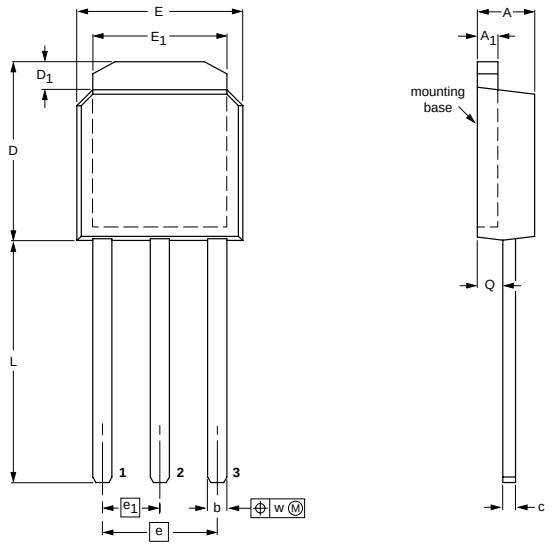


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

MECHANICAL DATA

Plastic single-ended package (Philips version of I-PAK); 3 leads (in-line) **SOT533**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D	D_1	E	E_1	e	e_1	L	Q
mm	2.38 2.22	0.89 0.71	0.89 0.71	0.56 0.46	7.28 6.94	1.06 0.96	6.73 6.47	5.36 5.26	4.57	2.285	9.8 9.4	1.00 1.10

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT533		TO-251				99-02-18

Fig.13. SOT533, (I-PAK). Pin 2 connected to mounting base.

DEFINITIONS

DATA SHEET STATUS		
DATA SHEET STATUS[2]	**PRODUCT STATUS**[3]	**DEFINITIONS**
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A
Limiting values		
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		
© **Philips Electronics N.V. 2004**		
All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.		
The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.		

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

2 Please consult the most recently issued datasheet before initiating or completing a design.

3 The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

Copyright © Each Manufacturing Company.

All Datasheets cannot be modified without permission.

This datasheet has been download from :

www.AllDataSheet.com

100% Free DataSheet Search Site.

Free Download.

No Register.

Fast Search System.

www.AllDataSheet.com